

13. (Amended) A method for patterning a thin film using a resist pattern as defined in claim 1.

16. (Amended) A patterning method as defined in claim 14, wherein the pre-resist pattern and the resist pattern have their respective T-shaped or reversed trapezoid longitudinal cross sections.

19. (Amended) A patterning method as defined in claim 17, wherein the ashing treatment is carried out by using a process gas composed of oxygen gas containing at least one of fluorine-based gas and nitrogen/hydrogen gas mixture.

20. (Amended) A patterning method as defined in claim 17, wherein the pre-resist pattern and the resist pattern have their respective T-shaped or reversed trapezoid longitudinal cross sections.

23. (Amended) A patterning method as defined in claim 21, wherein the pre-resist pattern and the resist pattern have their respective T-shaped or reversed trapezoid longitudinal cross sections.

26. (Amended) A patterning method as defined in claim 24, wherein the pre-resist pattern and the resist pattern have their respective T-shaped or reversed trapezoid longitudinal cross sections.

29. (Amended) A patterning method as defined in claim 27, wherein the ashing treatment is carried out by using a process gas composed of oxygen gas containing at least one of fluorine-based gas and nitrogen/hydrogen gas mixture.

30. (Amended) A patterning method as defined in claim 27, wherein the pre-resist pattern and the resist pattern have their respective T-shaped or reversed trapezoid longitudinal cross sections.

33. (Amended) A patterning method as defined in claim 31, wherein the pre-resist pattern and the resist pattern have their respective T-shaped or reversed trapezoid longitudinal cross sections.

36. (Amended) A patterning method as defined in claim 34, wherein the pre-resist pattern and the resist pattern have their respective T-shaped or reversed trapezoid longitudinal cross sections.

39. (Amended) A patterning method as defined in claim 37, wherein the ashing treatment is carried out by using a process gas composed of oxygen gas containing at least one of fluorine-based gas and nitrogen/hydrogen gas mixture.

40. (Amended) A patterning method as defined in claim 37, wherein the pre-resist pattern and the resist pattern have their respective T-shaped or reversed trapezoid longitudinal cross sections.

43. (Amended) A patterning method as defined in claim 41, wherein the pre-resist pattern and the resist pattern have their respective T-shaped or reversed trapezoid longitudinal cross sections.

44. (Amended) A method for manufacturing a micro device, using a patterning method for a thin film as defined in claim 13.